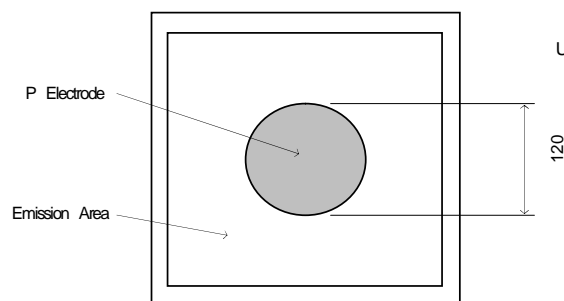
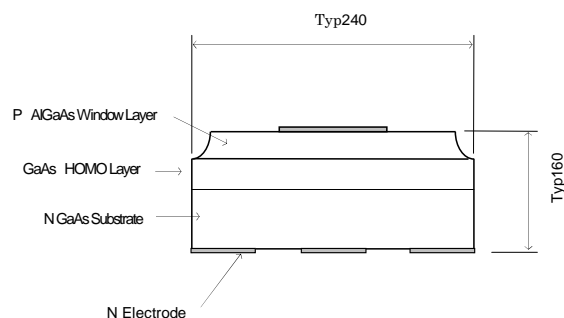


Radiation	Type	Electrodes
Infrared	AlGaAs/GaAs	P (anode) up



UNIT: m



Physical Characteristics & Structure

Material: AlGaAs/GaAs Bond Pad Size: 120um diameter
 Junction Size: 240um x 240um Anode Metalization: Gold Alloy
 Thickness: 160um Cathode Metalization: Gold Alloy

Electrical & Optical Characteristics (Ta = 25°C)

ITEMS	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Forward Voltage	V _f	I _f =20mA	--	--	1.5	V
Reverse Voltage	V _r	I _r =5uA	5	--	--	V
Radiant Power*	Φ _e	I _f =20mA	1.5	--	--	mW
Peak Wavelength	λ _p	I _f =20mA	--	940	--	nm
Spectral Bandwidth at 50%	Δλ _{0.5}	I _f =20mA	--	55	--	nm

* LED chip is mounted on TO-18 gold header without resin coating.

Absolute Maximum Ratings (Ta = 25°C)

Continuous Maximum Forward Current: 50mA (DC)
 Reverse Voltage: 5V (I_R=10uA)
 Storage Temperature
 while on mylar membrane: 0 to 40 °C
 after removal from mylar membrane: -30 to 100 °C



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.

2014-04-24